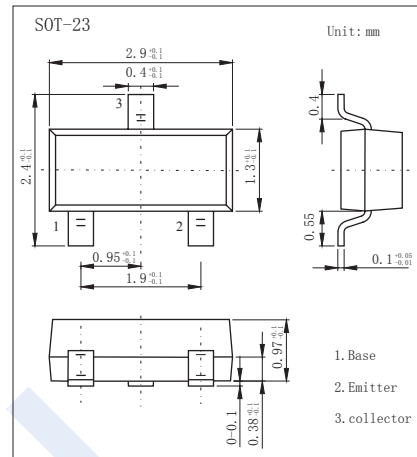


PNP Transistors

2SB710A

■ Features

- Large collector current I_c
- Complimentary to 2SD602A.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-50	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_c	-500	mA
Collector current - Pulse	I_{CP}	-1	A
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_c = -100 \mu\text{A}, I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CEO}	$I_c = -10 \text{ mA}, I_B = 0$	-50			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -300 \text{ mA}, I_B = -30 \text{ mA}$		-0.35	-0.6	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -300 \text{ mA}, I_B = -30 \text{ mA}$		-1.1	-1.5	
DC current gain	h_{FE}	$V_{CE} = -10\text{V}, I_c = -150 \text{ mA}$	85		340	
		$V_{CE} = -10\text{V}, I_c = -500 \text{ mA}$	40			
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1 \text{ MHz}$		6	15	pF
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz

■ Classification of $h_{FE}(1)$

Type	2SB710A- Q	2SB710A- R	2SB710A- S
Range	85-170	120-240	170-340
Marking	DQ	DR	DS

PNP Transistors

2SB710A

■ Typical Characteristics

